



JST41T-800BW 40

Peak gate power	P_{GM}	40	W
Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	1.5	kV

($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V R_L=33$	- -	MAX.	50	mA
V_{GT}		- -	MAX.	1.3	V
V_{GD}	$V_D=V_{DRM} T_j=125$ $R_L=3.3k$	- -	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	80	mA
				200	
I_H	$I_T=500mA$		MAX.	100	mA
dV/dt	$V_D=540V$ Gate Open $T_j=125$		MIN.	2000	V/ μs

	J	ST	41	T	-800	BW
JieJie Microelectronics Co., Ltd.		Triacs				
		$I_{T(RMS)}:40A$				
				$T:TG-C(Ins)$		
						$BW:IGT1-3 \quad 50mA$
					$800:V_{DRM} / V_{RRM} \quad 800V$	

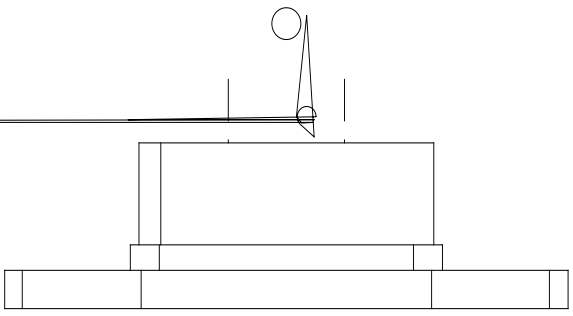
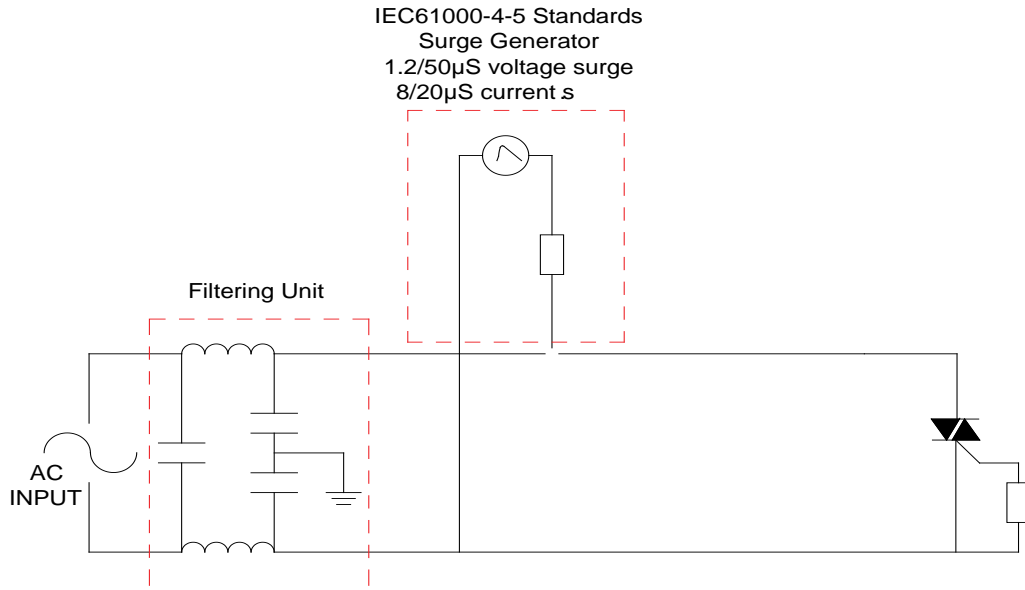


FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



Order code	Voltage $V_{DRM}/V_{RRM}(V)$	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		- -			
JST41T-800BW	800	50	TG-C(Ins)	10	Tube

Document Revision History

Date	Revision	Changes
Apr.11, 2023	A.1.0	

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